

IN THE SPECIFICATION:

Please rewrite paragraph 0054 as follows:

-- In FIG. 2, reference numeral 100 denotes a layered substrate to be transferred. The layered substrate 100 includes a semiconductor substrate ~~[[100]]~~ 101, device layer 102 which can be terminated with a layer 103 that comprises at least one metallic element such as Ti, Ta, Zr, Hf, silicides, nitrides and conducting siliconnitrides of the aforementioned elemental metals; Cu, W, Al, composites of these metals with glass; and any combination thereof. Preferably, layer 103 comprises Cu. The metallic element of layer 103 may be patterned, i.e., a patterned wiring level, or a blanket layer. When a patterned metallic element is present, portions of layer 103 may be comprised of an insulating material including oxides, nitrides, oxynitrides, polymeric dielectrics and inorganic dielectrics. The insulating material may be porous or non-porous. The layered substrate 100 is fabricated using any well-known semiconductor processing technique. --